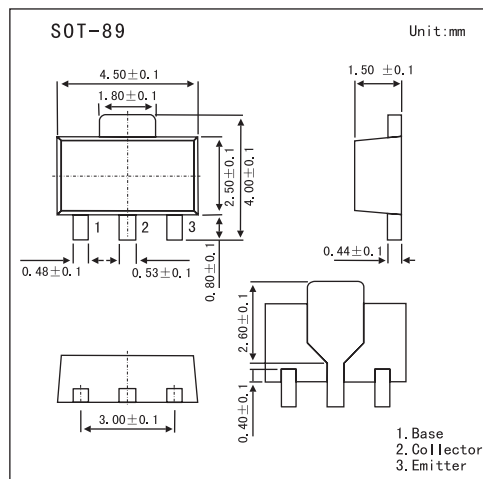


2SC4132

Features

- High breakdown voltage
- Low collector output capacitance
- High transition frequency Ft=80MHz)



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
collector-base voltage	V _{CB0}	120	V
collector-emitter voltage	V _{CE0}	120	V
emitter-base voltage	V _{EB0}	5	V
collector current	I _c	2	A
	I _{cP}	3	A *1
CollectorPower Dissipation	P _c	0.5	W *2
		2	W
Junction Temperature	T _J	150	°C
storage Temperature	T _{stg}	-55 to 150	°C

*1 Single pulse pw=10ms

*2 When mounted on a 40X40X0.7 mm ceramic board.

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV _{CB0}	I _c =50μA	120			V
collector-emitter breakdown voltage	BV _{CE0}	I _c =1mA	120			V
Emitter-base breakdown voltage	BV _{EB0}	I _E =50μA	5			V
Collector cutoff current	I _{CB0}	V _{CB} =100V			1	μA
Emitter out current	I _{EB0}	V _{EB} =4V			1	μA
Emitter-emitter saturation voltage	V _{CE(sat)}	I _c /I _B =1A/0.1A			0.4	V
DC current transfer ratio	h _{FE}	V _{CE} /I _c =5V/0.1A	82		390	
Transition frequency	f _t	V _{CE} =5V, I _E =-0.1A, f=30MHz		80		MHz
Output capacitance	C _{ob}	V _{CB} =10V, I _E =0A, f=1MHz		20		pF

hFE Classification

TYPE	CBP	CBQ	CBR
Rank	P	Q	R
Marking	82 to 180	120 to 270	180 to 390